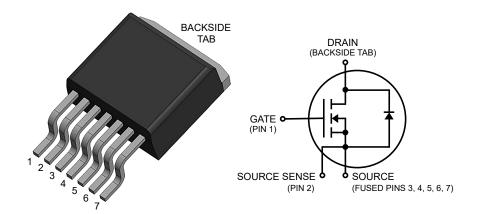
700V, 60 mΩ N-Channel mSiC[™] MOSFET

MSC060SMA070SD



Product Overview

700V, 60 m Ω typical at V_{GS} = 20V, 68 m Ω typical at V_{GS} = 18V, Silicon Carbide (SiC) N-Channel MOSFET, TO-263 7-lead XL with a source sense.



Features

- AEC-Q101 qualified option available
- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, T_{I(max)} = 175 °C
- · Fast and reliable body diode
- Superior avalanche ruggedness
- · RoHS compliant

Benefits

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- · Induction heating and welding
- Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

1. Device Specifications

This section shows the specifications of this device.

1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Table 1-1. Absolute Maximum Ratings

| Symbol | Parameter | Ratings | Unit |
|-----------------|---|-----------|------|
| V_{DSS} | Drain source voltage | 700 | V |
| I _D | Continuous drain current at T _C = 25 °C | 51 | Α |
| | Continuous drain current at T _C = 100 °C | 36 | |
| I _{DM} | Pulsed drain current ¹ | 188 | |
| V_{GS} | Gate-source voltage | 23 to -10 | V |
| | Transient gate-source voltage | 25 to -12 | |
| P _D | Total power dissipation at T _C = 25 °C | 240 | W |
| | Linear derating factor | 1.6 | W/°C |

Note:

1. Repetitive rating: pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

| Symbol | Characteristic/Test Conditions | Min. | Тур. | Max. | Unit |
|------------------|-------------------------------------|------|------|------|------|
| $R_{\theta JC}$ | Junction-to-case thermal resistance | _ | 0.48 | 0.62 | °C/W |
| Tj | Operating junction temperature | -55 | _ | 175 | °C |
| T _{STG} | Storage temperature | -55 | _ | 175 | |
| _ | Reflow temperature | _ | _ | 260 | °C |
| Wt | Package weight | _ | 1.6 | _ | g |

ESD practices should comply with JESD-625.

1.2 Electrical Performance

The following table shows the static characteristics of this device. $T_J = 25$ °C unless otherwise specified.

Table 1-3. Static Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Тур. | Max. | Unit |
|----------------------|---|---|----------|------|------|------|
| V _{(BR)DSS} | Drain-source breakdown voltage | $V_{GS} = 0V, I_D = 100 \mu A$ | 700 | _ | _ | V |
| R _{DS(on)} | Drain-source on resistance ¹ | V _{GS} = 20V, I _D = 20A | _ | 60 | 75 | mΩ |
| | | $V_{GS} = 18V, I_D = 20A$ | _ | 68 | _ | |
| V _{GS(th)} | Gate-source threshold voltage | $V_{GS} = V_{DS}$, $I_D = 1 \text{ mA}$ | 1.9 | 3.0 | 5.0 | V |
| I _{DSS} | Zero gate voltage drain current | V _{DS} = 700V, V _{GS} = 0V | _ | 0.1 | 25 | μΑ |
| | | V _{DS} = 700V, V _{GS} = 0V, T _J = 175 °C | <u> </u> | 1.5 | _ | |
| I _{GSS} | Gate-source leakage current | V _{GS} = 20V/–10V | _ | _ | ±100 | nA |

Note:

1. Pulse test: pulse width < 380 μ s, duty cycle < 2%.



The following table shows the dynamic characteristics of this device. T_J = 25 °C unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating V_{GS} = 20V/–5V.

Table 1-4. Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Тур. | Max. | Unit |
|---------------------|-----------------------------------|---|------|------|----------|------|
| C _{iss} | Input capacitance | $V_{GS} = 0V$ | _ | 1160 | _ | pF |
| C _{rss} | Reverse transfer capacitance | V _{DD} = 700V | _ | 10 | _ | |
| C _{oss} | Output capacitance | $V_{AC} = 25 \text{ mV}$ f = 200 kHz | _ | 132 | _ | |
| Q _G | Total gate charge | V _{GS} = -5V/20V | _ | 56 | | nC |
| Q_{GS} | Gate-source charge | V _{DD} = 470V | _ | 15 | _ | |
| Q _{GD} | Gate-drain charge | I _D = 20A | _ | 9.0 | _ | |
| t _{d(on)} | Turn-on delay time | V _{DD} = 470V | _ | 10 | _ | ns |
| t _r | Voltage rise time | V _{GS} = -5V/20V | _ | 7.0 | _ | |
| t _{d(off)} | Turn-off delay time | I _D = 20A | _ | 19 | _ | |
| t _f | Voltage fall time | $R_{G(ext)} = 4\Omega$ | _ | 7.0 | _ | |
| E _{on} | Turn-on switching energy | Freewheeling diode = $MSC060SMA070SD (V_{GS} = -5V);$ | _ | 92 | _ | μJ |
| E _{off} | Turn-off switching energy | reference Figure 1-19 | _ | 11 | _ | |
| ESR | Gate equivalent series resistance | f = 1 MHz, 25 mV, drain short | _ | 2.6 | _ | Ω |
| SCWT | Short circuit withstand time | V _{DS} = 560V, V _{GS} = 20V | _ | 3.0 | _ | μs |
| E _{AS} | Avalanche energy, single pulse | I _D = 20A | _ | 1100 | _ | mJ |

The following table shows the body diode characteristics of this device. $T_J = 25$ °C unless otherwise specified. The body diode reverse recovery is characterized, not 100% tested.

Table 1-5. Body Diode Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Тур. | Max. | Unit |
|------------------|--------------------------|--|------|------|------|------|
| V_{SD} | Diode forward voltage | I _{SD} = 20A, V _{GS} = 0V | _ | 3.7 | _ | ٧ |
| | | I _{SD} = 20A, V _{GS} = -5V | _ | 3.9 | 5.0 | |
| t _{rr} | Reverse recovery time | I_{SD} = 20A, V_{GS} = -5V, Drive R_G = 8Ω , V_{DD} = | _ | 10 | _ | ns |
| Q _{rr} | Reverse recovery charge | 470V, dI/dt = –8000 A/μs | _ | 336 | _ | nC |
| I _{RRM} | Reverse recovery current | | _ | 54 | _ | Α |



1.3 Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

Figure 1-1. Drain Current vs. V_{DS} at T_{J}

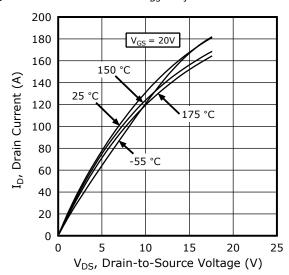


Figure 1-2. Drain Current vs. V_{DS} at V_{GS}

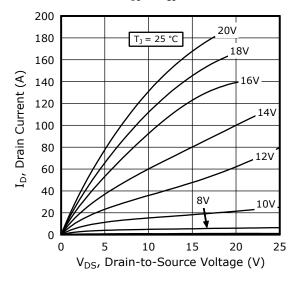


Figure 1-3. Drain Current vs. V_{DS} at V_{GS}

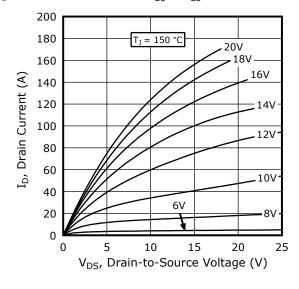


Figure 1-4. Drain Current vs. V_{DS} at V_{GS}

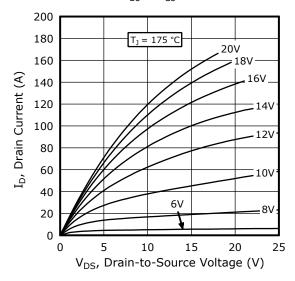


Figure 1-5. R_{DS(on)} vs. Junction Temperature

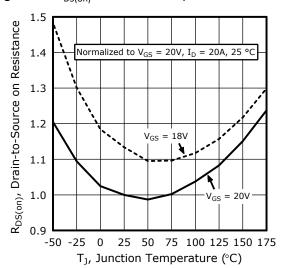


Figure 1-6. Gate Charge Characteristics

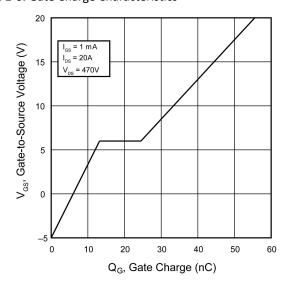


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

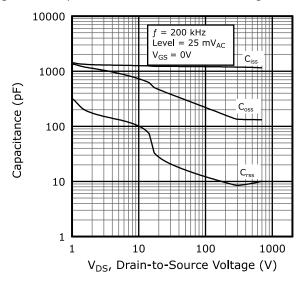


Figure 1-8. Output Charge vs. Drain-to-Source Voltage

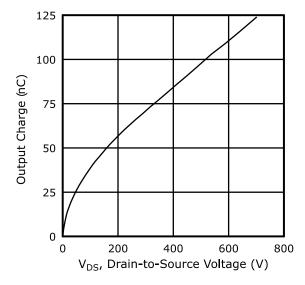




Figure 1-9. Output Stored Energy vs. V_{DS}

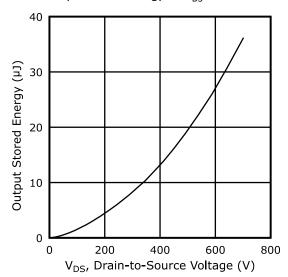


Figure 1-10. I_D vs. V_{DS} 3rd Quadrant Conduction

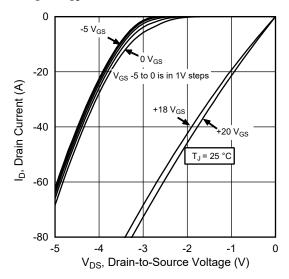


Figure 1-11. I_D vs. V_{DS} 3rd Quadrant Conduction

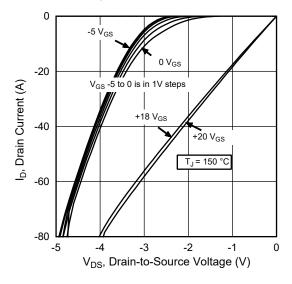


Figure 1-12. Switching Energy E_{on} vs. $V_{DS} \& I_{D}$

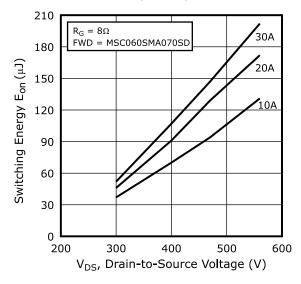




Figure 1-13. Switching Energy E_{off} vs. $V_{DS} \& I_{D}$

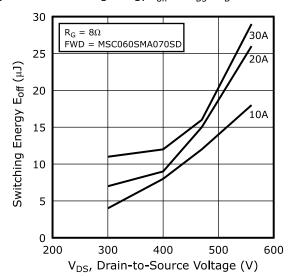


Figure 1-14. Switching Energy vs. R_G

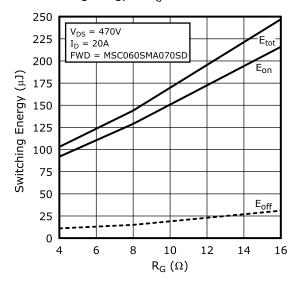


Figure 1-15. Switching Energy vs. Junction Temperature

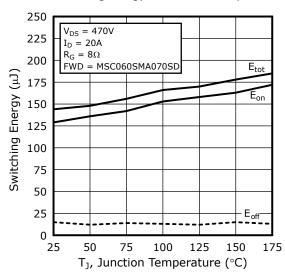


Figure 1-16. Threshold Voltage vs. Junction Temperature

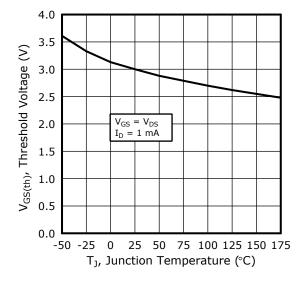




Figure 1-17. Forward Safe Operating Area

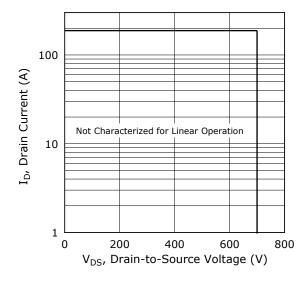
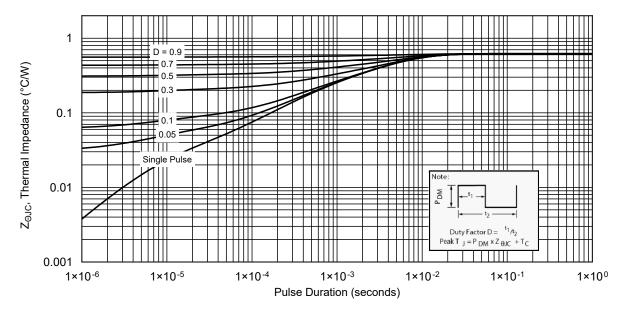
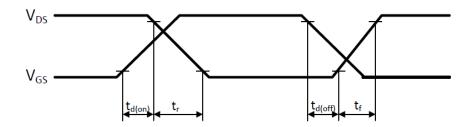


Figure 1-18. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of this device.

Figure 1-19. Switching Waveform





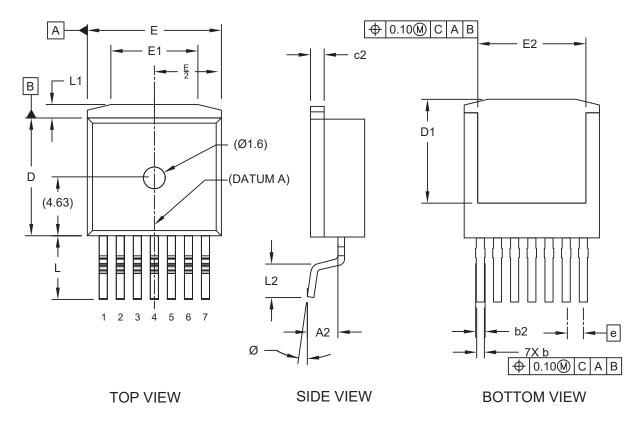
2. Package Specification

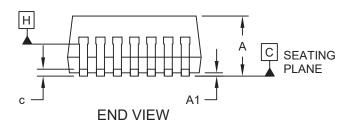
This section shows the package specification of this device.

2.1 Package Outline Drawing

The following figure illustrates the TO-263-7L XL package outline of this device.

Figure 2-1. Package Outline Drawing





The following table shows the TO-263-7L XL dimensions and should be used in conjunction with the package outline drawing.

Table 2-1. TO-263-7L XL Dimensions

| Symbol | Description | Min. (mm) | Max. (mm) |
|--------|-----------------|-----------|-----------|
| N | Number of leads | 7 | |
| е | Pitch | 1.27 BSC | |



| co | continued | | | | |
|--------|-----------------------------|-----------|-----------|--|--|
| Symbol | Description | Min. (mm) | Max. (mm) | | |
| Α | Overall height | 4.30 | 4.70 | | |
| A1 | Seating plane height | _ | 0.25 | | |
| A2 | Seating plane to lead | 2.20 | 2.60 | | |
| b | Lead width | 0.52 | 0.72 | | |
| b1 | | 0.60 | 0.80 | | |
| С | Lead thickness | 0.42 | 0.62 | | |
| c2 | Thermal pad thickness | 1.07 | 1.47 | | |
| L | Lead length | 4.55 | 4.95 | | |
| L1 | Tab length | 0.87 | 1.27 | | |
| L2 | Foot length | 2.48 | 2.88 | | |
| D | Molded body length | 9.05 | 9.45 | | |
| D1 | Thermal pad length | 7.58 | 7.98 | | |
| Е | Total width | 9.80 | 10.20 | | |
| E1 | Thermal pad width step back | 6.30 | 6.70 | | |
| E2 | Thermal pad width | 7.80 | 8.20 | | |
| Ø | Lead foot angle | 0° | 8° | | |

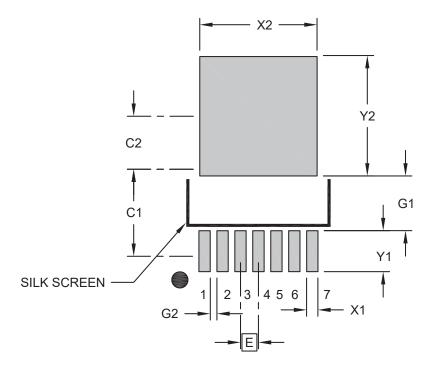
Note: Dimensioning and tolerancing per ASME Y14.5M.

• BSC: Basic dimension. Theoretically exact value shown without tolerances.

2.2 Recommended Land Pattern

The following figure illustrates the recommended land pattern of this device.

Figure 2-2. Recommended Land Pattern



The following table shows the recommended land pattern dimensions.



Table 2-2. Recommended Land Pattern Dimensions

| Symbol | Description | Min. (mm) | Nom. (mm) | Max. (mm) |
|--------|---------------------------------|-----------|-----------|-----------|
| E | Contact pitch | 1.27 BSC | | |
| X2 | Center pad width | _ | _ | 8.30 |
| Y2 | Center pad length | _ | _ | 8.45 |
| C1 | Contact pad spacing | _ | 6.45 | _ |
| C2 | Contact pad spacing | _ | 4.30 | _ |
| X1 | Contact pad width (X7) | _ | _ | 0.80 |
| Y1 | Contact pad length (X7) | _ | _ | 2.90 |
| G1 | Contact pad to center pad (X7) | 3.88 | _ | _ |
| G2 | Contact pad to contact pad (X6) | 0.47 | _ | _ |

Notes:

- Dimensioning and tolerancing per ASME Y14.5M.
 - BSC: Basic dimension. Theoretically exact value shown without tolerances.
- For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process.



3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

| Revision | Date | Description |
|----------|---------|--------------------------------------|
| С | 07/2024 | Added 2.2. Recommended Land Pattern. |
| В | 05/2024 | Updated Figure 1-5. |
| A | 04/2024 | Initial revision |



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